

## Cation Distribution in $(M', M)_3\text{Se}_4$

### II. $(\text{V}, \text{Ti})_3\text{Se}_4$ and $(\text{Cr}, \text{V})_3\text{Se}_4$

A. HAYASHI, Y. UEDA, AND K. KOSUGE

*Department of Chemistry, Faculty of Science,  
Kyoto University, Kyoto, Japan*

H. MURATA AND H. ASANO

*Institute of Materials Science, University of Tsukuba, Sakura-mura,  
Niihari-gun, Ibaraki, Japan*

N. WATANABE

*National Laboratory for High Energy Physics, Oho-machi, Tsukuba-gun,  
Ibaraki, Japan*

AND F. IZUMI

*National Institute for Research in Inorganic Materials, Sakura-mura,  
Niihari-gun, Ibaraki, Japan*

Received November 11, 1986; in revised form February 18, 1987

The cation distribution among the two crystallographic cation sites of the  $\text{Cr}_3\text{S}_4$  structure was determined in  $\text{VTi}_2\text{Se}_4$  and  $\text{VCr}_2\text{Se}_4$  by high-resolution neutron diffraction, using Rietveld analysis. The results showed a considerable disorder but they nevertheless revealed the site preference of V atoms for the  $2(a)$  site in both compounds. The compositional changes of the lattice parameters and the transition temperatures to the  $\text{CdI}_2$ -type structure in  $(\text{V}_x\text{Ti}_{1-x})_3\text{Se}_4$  and  $(\text{Cr}_x\text{V}_{1-x})_3\text{Se}_4$  were compared with those in  $(\text{Cr}_x\text{Ti}_{1-x})_3\text{Se}_4$  and  $(\text{Fe}_x\text{Cr}_{1-x})_3\text{Se}_4$ , and discussed from the viewpoint of the site preference of the cation. © 1987 Academic Press, Inc.

### Introduction

Most of the  $3d$ -transition metal chalcogenides with chemical formula  $M_3X_4$  ( $M$ :  $3d$ -transition metal,  $X$ : S, Se, Te) have the spinel structure or the  $\text{Cr}_3\text{S}_4$  structure, as shown in Table I. The chalcogenide stacking is  $ccp$  for the spinel structure and  $hcp$  for the  $\text{Cr}_3\text{S}_4$  structure. In both structures,

there are two crystallographic sites for metal ions and these compounds are expressed as  $(M)[M_2]X_4$  based on the distinction of sites occupied by metal ions. In the expression  $(M)[M_2]X_4$ , ( ) and [ ] denote tetrahedral and octahedral voids in the spinel structure, respectively. In contrast, both ( ) and [ ] denote octahedral voids in the  $\text{Cr}_3\text{S}_4$  structure. The characteristic of

the  $\text{Cr}_3\text{S}_4$  structure is that it is vacancy-ordered, which has been evidenced from the observation of the phase transition from the  $\text{Cr}_3\text{S}_4$  to  $\text{CdI}_2$  type at higher temperatures in several compounds (1-4). Like other compounds with similar vacancy-ordered structures based on the  $\text{CdI}_2$  structure,  $M_5X_8$ ,  $M_2X_3$ ,  $M_7X_8$ , etc., have also been found in several  $\text{MX}-\text{MX}_2$  systems (5, 6). These structures are easily understood by following general principles. In the intermediate composition  $M_{1+y}X_2$  ( $0 < y < 1$ ) between  $\text{MX}$  with the NiAs structure and  $\text{MX}_2$  with the  $\text{CdI}_2$  structure, excess metal atoms of fraction  $y$  partially occur in the unoccupied layer (van der Waals' gap) in the  $\text{CdI}_2$  structure and are regularly arranged because of metal-vacancy or metal-metal interactions. The  $\text{Cr}_3\text{S}_4$  structure appears at  $y = 0.5$ , and the layer stacking in this structure is expressed as  $M^F X M^V X M^F X \dots$ , where  $M^F$  denotes the metal layer fully occupied (4*i*) sites and  $M^V$  the half-filled and ordered metal layer (2*a*) sites (see Fig. 1). The unit cell is described in terms of the basic  $\text{CdI}_2$  structure as  $a_m \approx \sqrt{3}a_h$ ,  $b_m \approx a_h$ , and  $c_m \approx 2c_h$ , where  $a_m$ ,  $b_m$ , and  $c_m$  are the lattice parameters of the  $\text{Cr}_3\text{S}_4$  structure having the monoclinic space group  $I2/m$ ;  $a_h$  and  $c_h$  are lattice parameters of the hexago-

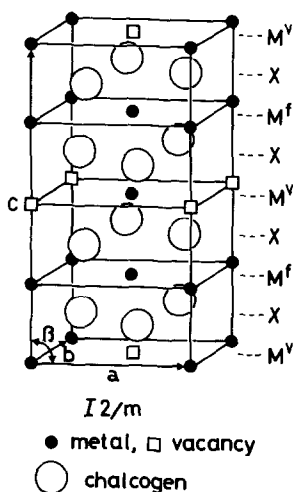


FIG. 1.  $\text{Cr}_3\text{S}_4$  structure ( $I2/m$ ).

TABLE I  
CRYSTAL STRUCTURE OF  $M_3X_4$  COMPOUNDS

X	M						
	Ti	V	Cr	Mn	Fe	Co	Ni
S	—	$\text{Cr}_3\text{S}_4$	$\text{Cr}_3\text{S}_4$	—	Spinel	Spinel	Spinel
Se	$\text{Cr}_3\text{S}_4$	$\text{Cr}_3\text{S}_4$	$\text{Cr}_3\text{S}_4$	—	$\text{Cr}_3\text{S}_4$	$\text{Cr}_3\text{S}_4$	$\text{Cr}_3\text{S}_4$
Te	$\text{Cr}_3\text{S}_4$	$\text{Cr}_3\text{S}_4$	$\text{Cr}_3\text{S}_4$	—	$\text{Cr}_3\text{S}_4$	$\text{CdI}_2$	$\text{CdI}_2$

nal  $\text{CdI}_2$  structure.

From the structural aspect, many mixed-metal compounds  $M'M_2X_4$  with the  $\text{Cr}_3\text{S}_4$  structure have also been synthesized and their physical properties have been studied. Chevreton and Andron (7) proposed such metal-ordered structures as normal-type  $(M')[M_2]X_4$  and inverse-type  $(M)[M'M]X_4$  on these compounds from analogy of spinel compound, where ( ) denotes the half-filled metal layer  $M^V$  and [ ] the filled metal layer  $M^F$ . In fact, such a metal-ordered structure has been confirmed in several compounds mainly by neutron diffraction or Mössbauer spectroscopy (7-13). To understand the physical properties and chemical bonds of these compounds, it is important to know the metal-ordered structure or site preference. In the phase diagram of the ternary  $M'-M-X$  system, the compound  $M'M_2X_4$  appears at the composition  $x = \frac{1}{3}$  in the pseudobinary system  $(M'_x M_{1-x})_3X_4$  or  $x = \frac{1}{2}$  in the system  $M'_x MX_2$  ( $0 < x < 1$ ). The site preference in  $M'M_2X_4$  may be kept also in the pseudobinary systems  $M'_3X_4-M_3X_4$  or  $M'_x MX_2$ . We have also systematically studied the phase diagram and physical properties of the selenide system  $(M'_x M_{1-x})_3\text{Se}_4$ , because most of 3*d*-transition metal selenides  $M_3\text{Se}_4$  crystallize in the  $\text{Cr}_3\text{S}_4$  structure (see Table I). In a previous paper (14), it was suggested that the compositional dependence of lattice parameters in  $(\text{Cr}_x\text{Ti}_{1-x})_3X_4$  ( $X$ : Se, Te) gives us information about the metal-ordered structure of  $\text{CrTi}_2\text{Se}_4$ ,  $\text{TiCr}_2\text{Se}_4$ ,  $\text{CrTi}_2\text{Te}_4$ , and  $\text{TiCr}_2\text{Te}_4$ . In a succeeding paper (15), the cation distribution in  $\text{CrTi}_2\text{Se}_4$  and  $\text{TiCr}_2\text{Se}_4$  was reported from Rietveld analysis of

high-resolution neutron diffraction patterns, and the compositional dependence of magnetic properties in  $(\text{Cr}_x\text{Ti}_{1-x})_3\text{Se}_4$  was explained on the basis of the site preference of Cr ions for  $M^V$  layers. We proposed the existence of the compounds  $(\text{Co})[\text{Ti}_2]\text{Se}_4$ ,  $(\text{Ni})[\text{Ti}_2]\text{Se}_4$ , and  $(\text{Ni})[\text{V}_2]\text{Se}_4$  from a recent study of their phase diagrams (16).

In this paper, we report the cation distribution in  $\text{VTi}_2\text{Se}_4$  and  $\text{VCr}_2\text{Se}_4$ , determined from Rietveld analysis of high-resolution powder neutron diffraction patterns, together with the phase diagrams of  $(\text{V}_x\text{Ti}_{1-x})_3\text{Se}_4$  and  $(\text{Cr}_x\text{V}_{1-x})_3\text{Se}_4$  systems.

### Experimental

Sample preparation was reported elsewhere (14). Phase characterizations were made at room temperature by powder X-ray diffraction with monochromatic  $\text{CuK}\alpha$  radiation. Phase transitions at higher temperatures were detected by high-temperature X-ray diffraction *in situ* and differential thermal analysis (DTA). In order to

prevent oxidation or decomposition, samples were sealed in an evacuated silica capillary during the high-temperature X-ray diffraction measurement and in a cylindrical silica capsule during the DTA measurement. The neutron diffraction experiment was carried out with a high-resolution powder diffractometer HRP (17) at the KENS pulsed spallation neutron source in the National Laboratory for High Energy Physics. The experimental details have been reported in our previous paper (15).

### Results and Discussion

Both  $(\text{V}_x\text{Ti}_{1-x})_3\text{Se}_4$  and  $(\text{Cr}_x\text{V}_{1-x})_3\text{Se}_4$  systems exhibited a solid solution with the  $\text{Cr}_3\text{S}_4$  structure over a whole composition range. Figures 2a and 2b show lattice parameters ( $I2/m$ :  $a$ ,  $b$ ,  $c$ ,  $\beta$ ) vs composition curves for both systems, determined by the least-squares method using more than 10 X-ray diffraction peaks. DTA and high-temperature X-ray measurements revealed that all the samples show a phase transition

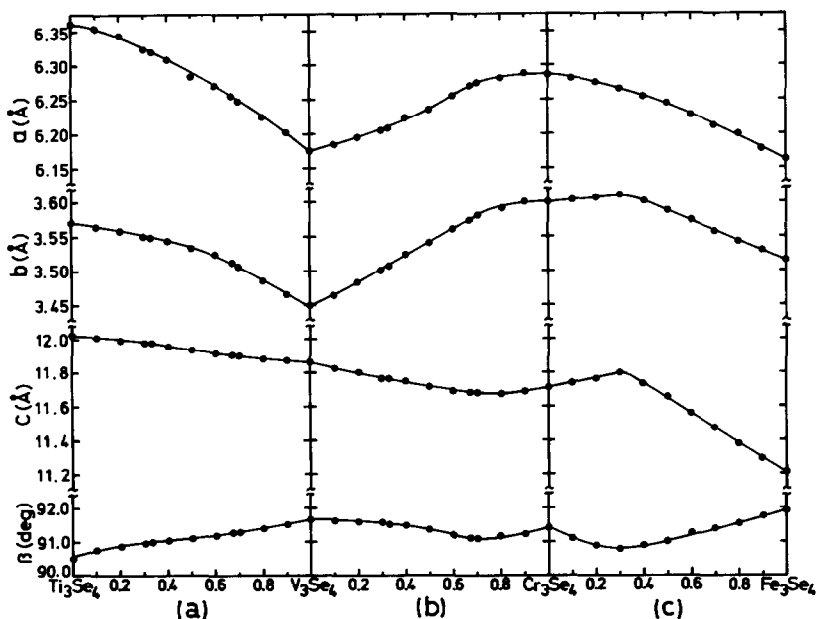


FIG. 2. Lattice parameters vs composition curves. (a)  $(\text{V}_x\text{Ti}_{1-x})_3\text{Se}_4$ ; (b)  $(\text{Cr}_x\text{V}_{1-x})_3\text{Se}_4$ ; and (c)  $(\text{Fe}_x\text{Cr}_{1-x})_3\text{Se}_4$ .

from the  $\text{Cr}_3\text{S}_4$  (monoclinic) to  $\text{CdI}_2$  (hexagonal) type accompanied by the disordering of vacancies. The hysteresis of the transition on heating and cooling was about  $10^\circ\text{C}$  for all samples. Phase diagrams obtained for both systems are shown in Figs. 3a and 3b.

$\text{VTi}_2\text{Se}_4$  and  $\text{VCr}_2\text{Se}_4$  were studied by neutron diffraction. The diffraction data were analyzed by the Rietveld method (18). Figures 4a and 4b show the observed and calculated profiles of the two compounds  $\text{VTi}_2\text{Se}_4$  and  $\text{VCr}_2\text{Se}_4$ , respectively. The final crystallographic parameters are given in Table II. The resulting cation distributions on two sites,  $M^V$  and  $M^F$ , are  $(\text{V}_{0.60}\text{Ti}_{0.40})[\text{V}_{0.40}\text{Ti}_{1.60}]\text{Se}_4$  for  $\text{VTi}_2\text{Se}_4$  and  $(\text{V}_{0.55}\text{Cr}_{0.45})[\text{V}_{0.45}\text{Cr}_{1.55}]\text{Se}_4$  for  $\text{VCr}_2\text{Se}_4$ . The results reveal that V atoms have a tendency to prefer the  $M^V$  layer in both  $\text{VTi}_2\text{Se}_4$  and  $\text{VCr}_2\text{Se}_4$ , although the cation distribution in both compounds is relatively disordered compared to the ideal one.

In selenides, it was determined by neutron diffraction that  $\text{CrTi}_2\text{Se}_4$  (15) and  $\text{FeCr}_2\text{Se}_4$  (11) are normal-type compounds and that  $\text{TiCr}_2\text{Se}_4$  (10, 14) is inverse type; that is, Cr ions in  $\text{CrTi}_2\text{Se}_4$  and  $\text{TiCr}_2\text{Se}_4$ ,

TABLE II  
FINAL ATOMIC PARAMETERS<sup>a</sup> FOR  $\text{VTi}_2\text{Se}_4$  AND  $\text{VCr}_2\text{Se}_4$  WITH ESTIMATED STANDARD DEVIATIONS IN PARENTHESES

Atom	Position	x	y	z	Occupancy
$\text{VTi}_2\text{Se}_4$					
V(1)	2(a)	0	0	0	0.60(2)
Ti(1)	2(a)	0	0	0	0.40(2)
V(2)	4(i)	0.2547(8)	0.226(2)	0	0.20(2)
Ti(2)	4(i)	0.2547(8)	0.226(2)	0	0.80(2)
Se(1)	4(i)	0.6304(3)	0.2976(6)	0	1.0
Se(2)	4(i)	0.8861(3)	0.2235(6)	0	1.0
$a' = 13.6153 \text{ \AA}; b' = 6.2962 \text{ \AA}; c' = 3.5562 \text{ \AA}; \gamma = 118.42^\circ$					
$B^b = 0.19(2) \text{ \AA}^2; R_{wp}^c = 5.15\%; R_B^d = 3.04\%$					
$\text{VCr}_2\text{Se}_4$					
V(1)	2(a)	0	0	0	0.55(1)
Cr(1)	2(a)	0	0	0	0.45(1)
V(2)	4(i)	0.2586(8)	0.238(2)	0	0.22(1)
Cr(2)	4(i)	0.2586(8)	0.238(2)	0	0.78(1)
Se(1)	4(i)	0.6338(3)	0.2974(7)	0	1.0
Se(2)	4(i)	0.8832(3)	0.2197(7)	0	1.0
$a' = 13.4049 \text{ \AA}; b' = 6.2801 \text{ \AA}; c' = 3.5784 \text{ \AA}; \gamma = 119.21^\circ$					
$B^b = 0.11(3) \text{ \AA}^2; R_{wp}^c = 8.11\%; R_B^d = 4.30\%$					

<sup>a</sup> In Rietveld analysis the reduced unit cell with space group  $B2/m$  was adopted. The relation between lattice parameters described in space group  $B2/m$  and  $I2/m$  is as follows:  $a = b'$ ,  $b = c'$ ,  $c = (a'^2 + b'^2 + 2a'b' \cos \gamma)^{1/2}$  and  $\beta = \cos^{-1}[(a' \cos \gamma + b')/c'^{1/2}]$ .

<sup>b</sup>  $B$  = overall thermal parameter.

<sup>c</sup>  $R_{wp} = [\sum_i w_i \{Y_i(\text{obs}) - Y_i(\text{cal})\}^2 / \sum_i w_i \{Y_i(\text{obs})\}^2]^{1/2}$ . ( $Y_i(\text{obs})$  and  $Y_i(\text{cal})$  are observed and calculated counts for the  $i$ th channel and  $w_i$  is a weighting factor.)

<sup>d</sup>  $R_B = \sum_k |I_k(\text{obs}) - I_k(\text{cal})| / \sum_k I_k(\text{obs})$ .  $I_k(\text{obs})$  and  $I_k(\text{cal})$  are observed and calculated integrated intensities for the  $k$ th reflection.

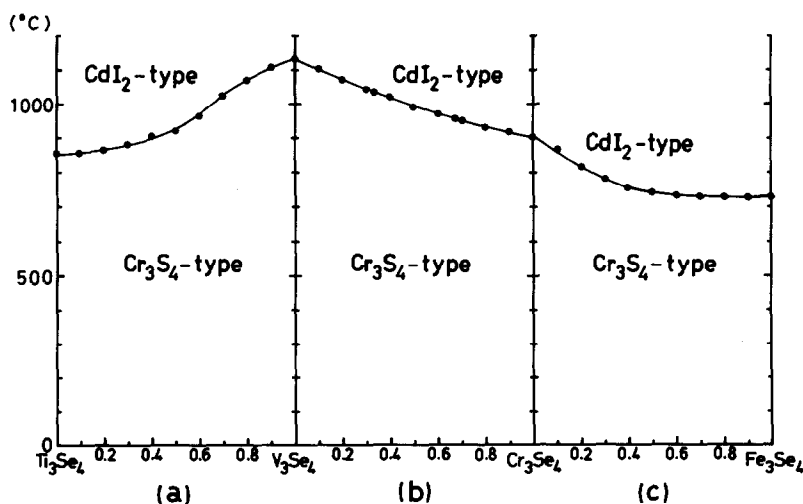


FIG. 3. Phase diagrams. (a)  $(\text{V}_x\text{Ti}_{1-x})_3\text{Se}_4$ ; (b)  $(\text{Cr}_x\text{V}_{1-x})_3\text{Se}_4$ ; and (c)  $(\text{Fe}_x\text{Cr}_{1-x})_3\text{Se}_4$ .

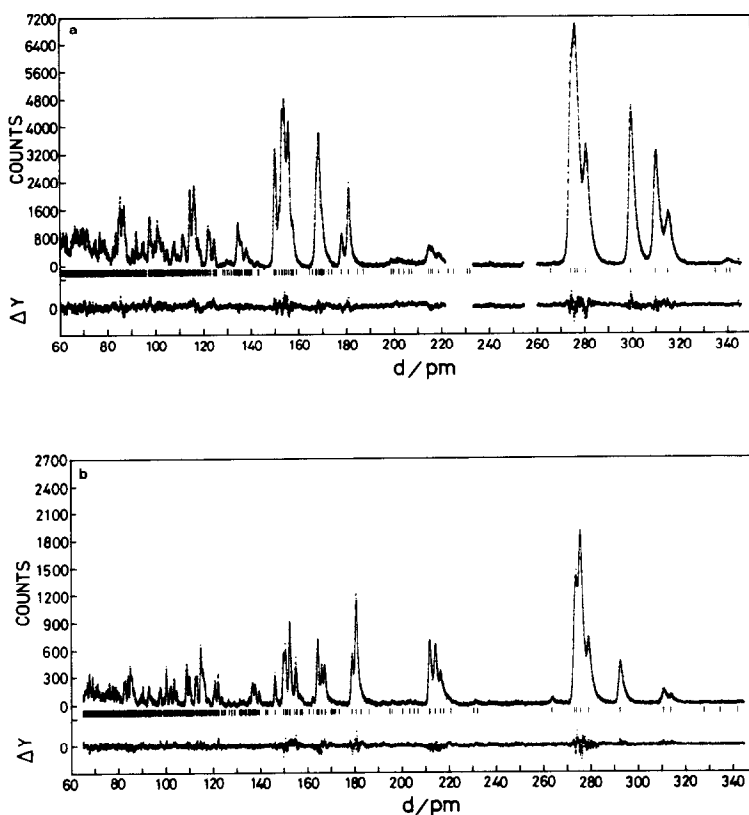


FIG. 4. Observed (dots) and calculated (solid lines) neutron diffraction patterns. (a)  $\text{VTi}_2\text{Se}_4$  and (b)  $\text{VCr}_2\text{Se}_4$ .  $\Delta Y$  shows the difference between observed and calculated counts. The vertical markers indicate Bragg positions. Diffraction data at around  $d = 225$  and  $258$  pm in (a) were omitted from the pattern because very weak peaks probably because of impurities appeared in these regions.

and Fe ions in  $\text{FeCr}_2\text{Se}_4$  preferentially occupy the  $M^V$  layer.

Now let us discuss the site preference or metal-ordered structure in  $(\text{Cr}_x\text{V}_{1-x})_3\text{Se}_4$  and  $(\text{V}_x\text{Ti}_{1-x})_3\text{Se}_4$  from  $\Delta c$  and  $\Delta T_c$  (defined below), in comparison with  $(\text{Cr}_x\text{Ti}_{1-x})_3\text{Se}_4$  and  $(\text{Fe}_x\text{Cr}_{1-x})_3\text{Se}_4$ . The compositional dependence of the lattice parameters and the phase diagram for  $(\text{Fe}_x\text{Cr}_{1-x})_3\text{Se}_4$  (19) are shown in Figs. 2c and 3c for reference. If the site preference is retained over the whole range of composition in the pseudo-binary solid solution  $(M'_xM_{1-x})_3X_4$  system and  $M'$  prefers to occupy the  $M^V$  layer, the substitution in the ideal case should progress as follows:

$$0 \leq x \leq \frac{1}{3} \quad (M'_{3x}M_{1-3x})(M_2)X_4$$

$$\frac{1}{3} \leq x \leq 1 \quad (M')(M'_{3x-1}M_{3-3x})X_4$$

with a turning point at  $x = \frac{1}{3}(M'M_2X_4)$ . As a measure of the site preference of metal ions, the compositional dependence of  $\Delta c^1 = [(\text{observed } c\text{-axis}) - (\text{Vegard's law})]$  is shown in Fig. 5 for  $(\text{V}_x\text{Ti}_{1-x})_3\text{Se}_4$  and  $(\text{V}_x\text{Cr}_{1-x})_3\text{Se}_4$ , together with  $(\text{Cr}_x\text{Ti}_{1-x})_3\text{Se}_4$  and  $(\text{Fe}_x\text{Cr}_{1-x})_3\text{Se}_4$ . In  $(\text{Cr}_x\text{Ti}_{1-x})_3\text{Se}_4$  and  $(\text{Fe}_x$

<sup>1</sup> The  $c$  parameter was adopted to discuss the deviation from the Vegard's law because it can be more precisely determined compared to the other lattice parameters using high angle (00 $l$ ) diffraction with stronger intensity and because it is more sensitive to changes in composition.

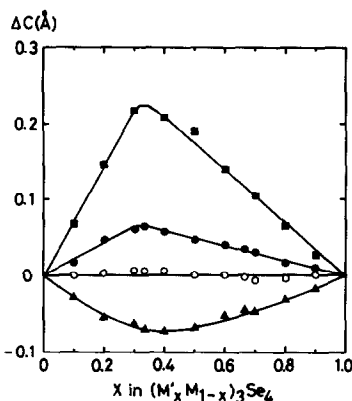


FIG. 5.  $\Delta c$  (see the text) vs composition curves of  $(M'_x M_{1-x})_3 \text{Se}_4$ .  $\circ$ ,  $(V_x \text{Ti}_{1-x})_3 \text{Se}_4$ ;  $\blacktriangle$ ,  $(V_x \text{Cr}_{1-x})_3 \text{Se}_4$ ;  $\bullet$ ,  $(\text{Cr}_x \text{Ti}_{1-x})_3 \text{Se}_4$ ;  $\square$ ,  $(\text{Fe}_x \text{Cr}_{1-x})_3 \text{Se}_4$ .

$\text{Cr}_{1-x})_3 \text{Se}_4$ ,  $\Delta c$  shows a linear change in the composition range for both  $0 < x < \frac{1}{2}$  and  $\frac{1}{2} < x < 1$ , as just obeying the Vegard's law between the intermediate compound  $\text{CrTi}_2 \text{Se}_4$  or  $\text{FeCr}_2 \text{Se}_4$  and the end members in each system. On the other hand,  $\Delta c \approx 0$  over the whole composition range in  $(V_x \text{Ti}_{1-x})_3 \text{Se}_4$  and there is a gradual change with a minimum around  $x = 0.4$  in  $(V_x \text{Cr}_{1-x})_3 \text{Se}_4$ . These observations suggest that substitution in both systems does not progress with so clear a site preference as in the other two systems. This is consistent with the results that the cation distribution observed in  $\text{VTi}_2 \text{Se}_4$  and  $\text{VCr}_2 \text{Se}_4$  is rather random.

In addition to the vacancy disordering, disordering of metal arrangement among the  $M^V$  and  $M^F$  layers can also be expected at a critical temperature  $T_i$ ; the degree of order naturally decreases with increasing temperature. The observed cation distribution corresponds to the degree of order at the temperature where the sample was annealed or at the lowest temperature where the diffusion of metal ions was possible. In DTA measurements, no anomaly corresponding to this transition was observed up to  $1100^\circ\text{C}$  in all samples. This means that the transition is of second order or  $T_i$  is

above  $1100^\circ\text{C}$ . The latter case is ruled out at least in  $\text{VTi}_2 \text{Se}_4$  and  $\text{VCr}_2 \text{Se}_4$ , as judged by the results that the observed cation distribution of the samples prepared at temperature as low as  $300^\circ\text{C}$  is rather random.

Figure 6 shows the deviation  $\Delta T$  defined as follows:

$$\Delta T = T_c - [(1-x)T_{c1} + xT_{c2}],$$

where  $x$  is the composition in  $(M'_x M_{1-x})_3 X_4$  system,  $T_c$  is the transition temperature from the  $\text{Cr}_3 \text{S}_4$  to  $\text{CdI}_2$  type and  $T_{c1}$  and  $T_{c2}$  are  $T_c$  for  $x = 0$  ( $M_3 X_4$ ) and  $x = 1$  ( $M'_3 X_4$ ), respectively. The curves show a minimum around  $x = \frac{1}{2}$  in  $(\text{Cr}_x \text{Ti}_{1-x})_3 \text{Se}_4$  and  $(\text{Fe}_x \text{Cr}_{1-x})_3 \text{Se}_4$  systems and around central composition ( $x = \frac{1}{2}$ ) in  $(V_x \text{Ti}_{1-x})_3 \text{Se}_4$  and  $(V_x \text{Cr}_{1-x})_3 \text{Se}_4$  systems. It is general in the solid solution system that  $\Delta T$  changes smoothly with a minimum or maximum around central composition in the case that no intermediate compound exists. If a compound exists at an intermediate composition,  $\Delta T$  changes in the same way between the intermediate compound and the end members.  $(\text{Cr}_x \text{Ti}_{1-x})_3 \text{Se}_4$  and  $(\text{Fe}_x \text{Cr}_{1-x})_3 \text{Se}_4$  systems seem to belong to the latter, having  $\text{CrTi}_2 \text{Se}_4$  and  $\text{FeCr}_2 \text{Se}_4$  with the metal-ordered structure as an intermediate compound. The former may be the case for  $(V_x \text{Ti}_{1-x})_3$

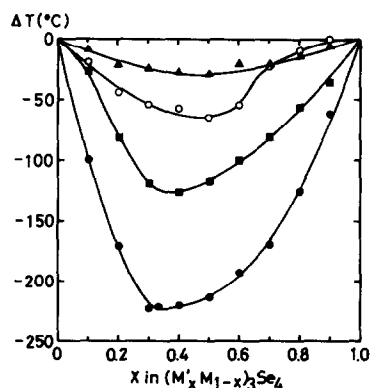


FIG. 6.  $\Delta T$  (see the text) vs composition curves of  $(M'_x M_{1-x})_3 \text{Se}_4$ .  $\circ$ ,  $(V_x \text{Ti}_{1-x})_3 \text{Se}_4$ ;  $\blacktriangle$ ,  $(V_x \text{Cr}_{1-x})_3 \text{Se}_4$ ;  $\bullet$ ,  $(\text{Cr}_x \text{Ti}_{1-x})_3 \text{Se}_4$ ;  $\square$ ,  $(\text{Fe}_x \text{Cr}_{1-x})_3 \text{Se}_4$ .

$\text{Se}_4$  and  $(\text{Cr}_x\text{V}_{1-x})_3\text{Se}_4$ . Therefore,  $T_t$  is likely to be higher than  $T_c$  in  $(\text{Cr}_x\text{Ti}_{1-x})_3\text{Se}_4$  and  $(\text{Fe}_x\text{Cr}_{1-x})_3\text{Se}_4$ , and lower in  $(\text{V}_x\text{Ti}_{1-x})_3\text{Se}_4$  and  $(\text{Cr}_x\text{V}_{1-x})_3\text{Se}_4$ . This is consistent with the results that cation distributions in  $\text{VTi}_2\text{Se}_4$  and  $\text{VCr}_2\text{Se}_4$  are more disordered than in  $\text{CrTi}_2\text{Se}_4$  and  $\text{TiCr}_2\text{Se}_4$  at the same annealing temperature of  $300^\circ\text{C}$ .

In conclusion, the cation distributions in  $\text{VTi}_2\text{Se}_4$  and  $\text{VCr}_2\text{Se}_4$  show considerable disorder but they nevertheless reveal the preference of V atoms for the  $M^V$  layer (2(a) sites). Further, Fe ions selectively occupy the  $M^V$  layer in  $(\text{Fe}_x\text{Cr}_{1-x})_3\text{Se}_4$ .

We have, at present, no explanation of the origin of such site preference; a key may be obtained when the site preference on all compounds with the  $\text{Cr}_3\text{S}_4$  structure and the physical properties of those compounds are made clear.

A neutron diffraction study at various temperatures to confirm the transition to the metal-disordered state, as well as a Mössbauer study of the compounds containing Fe as a constituent element to determine the cation distribution or the site preference, is now in progress.

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